Part Number Customer					
Category	Parameter		Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm		
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor	
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor	
	4.0	Secondary Flat Orientation	none	Wafer Vendor	
	5.0	Overall Thickness	436.00 +/- 11.00 μm	ADE, 100%	
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process	
	7.0	Bow	<60.00µm	Estimate ADE to ASTM F534, 100%	
	8.0	Warp	<60.00µm	Estimate ADE to ASTM F534, 100%	
	9.0	Edge Chips	0	Bright Light, 100%	
	10.0	Edge Exclusion	5mm		
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor	
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	13.0	Handle Thickness	400.00 +/- 10.00 μm	ADE, 100%	
	14.0	Handle Doping Type	Р	Wafer Vendor	
	15.0	Handle Dopant	Boron	Wafer Vendor	
	16.0	Handle Resistivity	0.01~0.02 Ohmcm	Wafer Vendor	
	17.0	Backside Finish	Polished with lasermark and oxide.	Guaranteed by process	
BuriedOxide	18.0	Oxide Type	Thermal		
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%	
	20.0	Oxide formed on	Handle		
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor	
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	23.0	Nominal Thickness	35.00 +/- 1.00 μm	Single point ADE, 100% (note3)	
	24.0	Distance to device silicon edge from wafer edge	< 2mm	Typical by Process	
	25.0	Device Doping Type	Р	Wafer Vendor	
	26.0	Device Dopant	Boron	Wafer Vendor	
	27.0	Device Resistivity	<0.005 Ohmem	Wafer Vendor	
	28.0	Surface Voids	None	Bright Light, 100% (note2)	
	29.0	Haze	None	Bright Light, 100% (note2)	
	30.0	Scratches	none on the front-side	Bright Light, 100% (note2)	

Icemos Technology Ltd

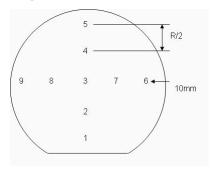
Product Specification

1000.698301

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information